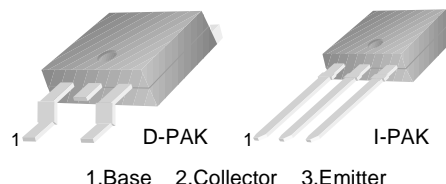


MJD29/29C

MJD29/29C

General Purpose Amplifier Low Speed Switching Applications

- Load Formed for Surface Mount Application (No Suffix)
- Straight Lead (I-PAK, "- I" Suffix)
- Electrically Similar to Popular TIP29 and TIP29C



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage		
	: MJD29	40	V
	: MJD29C	100	V
V_{CEO}	Collector-Emitter Voltage		
	: MJD29	40	V
	: MJD29C	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current (DC)	1	A
I_{CP}	Collector Current (Pulse)	3	A
I_B	Base Current	0.4	A
P_C	Collector Dissipation ($T_C=25^\circ\text{C}$)	15	W
	Collector Dissipation ($T_a=25^\circ\text{C}$)	1.56	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
$V_{CEO(sus)}$	*Collector-Emitter Sustaining Voltage				
	: MJD29	$I_C = 30\text{mA}, I_B = 0$	40		V
	: MJD29C		100		V
I_{CEO}	Collector Cut-off Current				
	: MJD29	$V_{CE} = 40\text{V}, I_B = 0$		50	μA
	: MJD29C	$V_{CE} = 60\text{V}, I_B = 0$		50	μA
I_{CES}	Collector Cut-off Current				
	: MJD29	$V_{CE} = 40\text{V}, V_{BE} = 0$		20	μA
	: MJD29C	$V_{CE} = 100\text{V}, V_{BE} = 0$		20	μA
I_{EBO}	Emitter Cut-off Current	$V_{BE} = 5\text{V}, I_C = 0$		1	mA
h_{FE}	*DC Current Gain	$V_{CE} = 4\text{V}, I_C = 0.2\text{A}$	40		
		$V_{CE} = 4\text{V}, I_C = 1\text{A}$	15	75	
$V_{CE(sat)}$	*Collector-Emitter Saturation Voltage	$I_C = 1\text{A}, I_B = 125\text{mA}$		0.7	V
$V_{BE(on)}$	*Base-Emitter ON Voltage	$V_{CE} = 4\text{A}, I_C = 1\text{A}$		1.3	V
f_T	Current Gain Bandwidth Product	$V_{CE} = 10\text{V}, I_C = 200\text{mA}$	3		MHz

* Pulse Test: $PW \leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Typical Characteristics

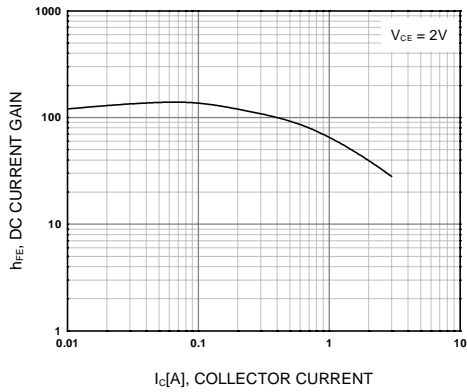


Figure 1. DC current Gain

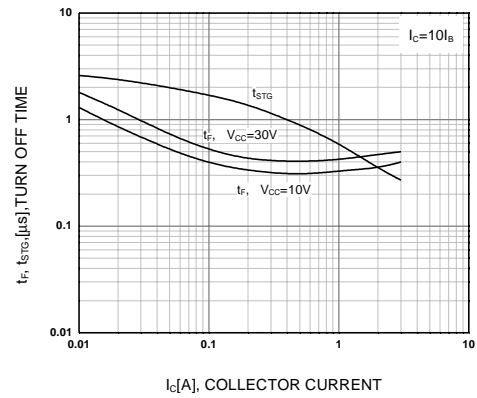


Figure 2. Turn On Time

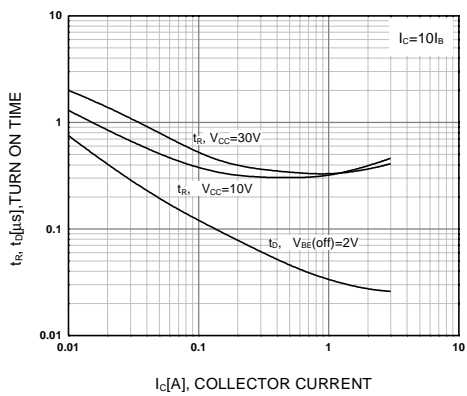


Figure 3. Turn Off Time

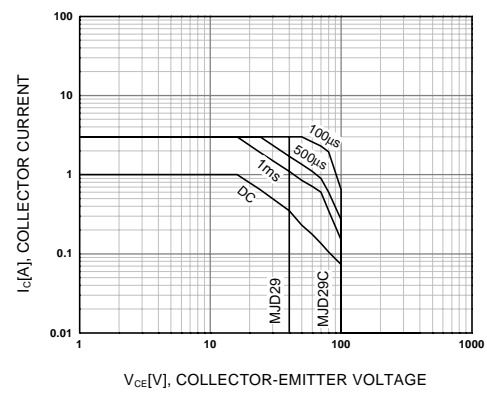


Figure 4. Safe Operating Area

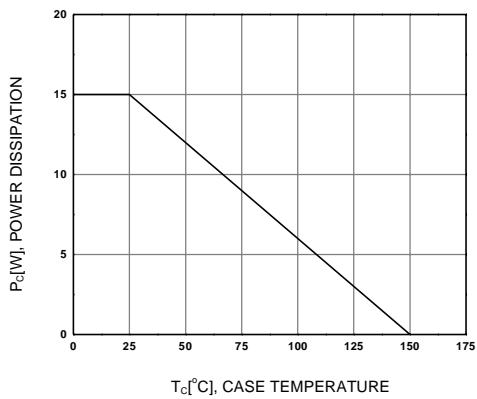


Figure 5. Power Derating

Technical drawing of the 230TYP component, showing three views: front, side, and top.

Front View Dimensions:

- Overall width: 6.60 ± 0.20
- Mounting tab width: 2.30 ± 0.20 (TYP)
- Central feature width: 5.34 ± 0.30
- Mounting tab height: 0.60 ± 0.20
- Central feature height: 2.70 ± 0.20
- Overall height: 9.50 ± 0.30
- Mounting tab offset: 0.76 ± 0.10
- Mounting tab depth: 0.80 ± 0.20
- Mounting tab width: 0.50
- Mounting tab height: 0.70 ± 0.20

Side View Dimensions:

- Overall width: 2.30 ± 0.10
- Mounting tab width: 0.50 ± 0.10
- Mounting tab height: 0.91 ± 0.10
- Mounting tab depth: 0.89 ± 0.10
- Mounting tab width: 0.50 ± 0.10
- Mounting tab height: 1.02 ± 0.20
- Mounting tab width: 2.30 ± 0.20
- Mounting tab height: 0.55 (MIN)

Top View Dimensions:

- Overall width: 6.60 ± 0.20
- Mounting tab width: 2.30 ± 0.20 (TYP)
- Central feature width: 5.34 ± 0.30
- Mounting tab height: 0.60 ± 0.20
- Central feature height: 2.70 ± 0.20
- Overall height: 9.50 ± 0.30
- Mounting tab offset: 0.76 ± 0.10
- Mounting tab depth: 0.80 ± 0.20
- Mounting tab width: 0.50
- Mounting tab height: 0.70 ± 0.20

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